

	Hits	Search Text	DBs
2	21	((substrate or wafer or device or platen) same (alignment near12 mark) same ((first near12 second) or (front near18 back) or (front\$4 near14 rear\$4))) and (((protective near5 layer) or (insulat\$4 near9 layer) or SiO\$3 or (silicon near6 \$4oxide)) same (mark or alignment)) and etch\$4 and (bond\$5 or stick\$4 or laminat\$5 or attach\$4 or adher\$5) and (lithograph\$6 or pattern\$4) and ((reverse or mirror) same (alignment near12 mark))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
3	38	((substrate or wafer or device or platen) same (alignment near12 mark) same ((first near12 second) or (front near18 back) or (front\$4 near14 rear\$4))) and (((protective near5 layer) or (insulat\$4 near9 layer) or SiO\$3 or (silicon near6 \$4oxide)) same (mark or alignment)) and etch\$4 and (lithograph\$6 or pattern\$4) and ((reverse or mirror) same (alignment near12 mark) same (substrate or wafer or surface))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
4	14	((substrate or wafer or device or platen) same (alignment near12 mark) same ((first near12 second) or (front near18 back) or (front\$4 near14 rear\$4))) and (((protective near5 layer) or (insulat\$4 near9 layer) or SiO\$3 or (silicon near6 \$4oxide)) same (alignment near15 mark)) and etch\$4 and (lithograph\$6 or pattern\$4) and ((reverse or mirror) same (alignment near12 mark) same (substrate or wafer or surface)) and trench\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
5	33	((substrate or wafer or device or platen) same (alignment near12 mark\$4) same ((first near12 second) or (front near18 back) or (front\$4 near14 rear\$4))) and (((protective near5 layer) or (insulat\$4 near9 layer) or SiO\$3 or (silicon near6 \$4oxide)) same (alignment near15 mark\$4)) and etch\$4 and ((alignment near14 mark\$4) same reflect\$4 same (aluminum or Al))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB